

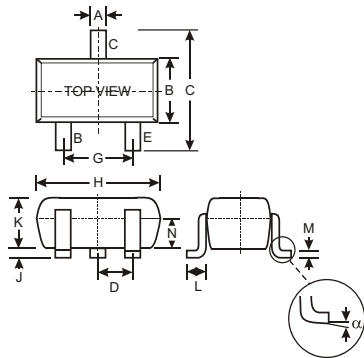
### Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTA)
- Built-In Biasing Resistor, R2 only
- Also Available in Lead Free Version

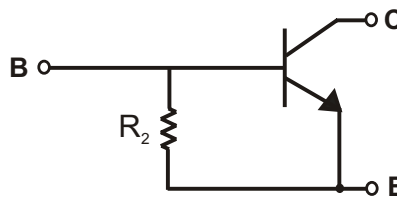
### Mechanical Data

- Case: SOT-523, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 3, on Page 2
- Terminal Connections: See Diagram
- Marking: Date Code and Marking Code (See Diagrams & Page 2)
- Weight: 0.002 grams (approx.)
- Ordering Information (See Page 2)

P/N	R2 (NOM)	MARKING
DDTC114GE	10K $\Omega$	N26
DDTC124GE	22K $\Omega$	N27
DDTC144GE	47K $\Omega$	N28
DDTC115GE	100K $\Omega$	N29



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
$\alpha$	0°	8°	—
All Dimensions in mm			



SCHEMATIC DIAGRAM

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub> (Max)	100	mA
Power Dissipation	P <sub>d</sub>	150	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R <sub>θJA</sub>	833	°C/W
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 1. Mounted on FR4 PC Board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

## Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV <sub>CBO</sub>	50	—	—	V	I <sub>C</sub> = 50μA
Collector-Emitter Breakdown Voltage		BV <sub>CEO</sub>	50	—	—	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage		BV <sub>EBO</sub>	5	—	—	V	I <sub>E</sub> = 720μA, DDTC114GE I <sub>E</sub> = 330μA, DDTC124GE I <sub>E</sub> = 160μA, DDTC144GE I <sub>E</sub> = 72μA, DDTC115GE
Collector Cutoff Current		I <sub>CBO</sub>	—	—	0.5	μA	V <sub>CB</sub> = 50V
Emitter Cutoff Current	DDTC114GE	I <sub>EBO</sub>	300	—	580	μA	V <sub>EB</sub> = 4V
	DDTC124GE		140		260		
	DDTC144GE		65		130		
	DDTC115GE		30		58		
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	—	—	0.3	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA
DC Current Transfer Ratio	DDTC114GE	h <sub>FE</sub>	30	—	—	—	I <sub>C</sub> = 5mA, V <sub>CE</sub> = 5V
	DDTC124GE		56				
	DDTC144GE		68				
	DDTC115GE		82				
Bleeder Resistor (R <sub>2</sub> ) Tolerance		ΔR <sub>2</sub>	-30	—	+30	%	—
Gain-Bandwidth Product*		f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz

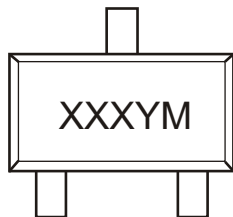
\* Transistor - For Reference Only

## Ordering Information (Note 2)

Device	Packaging	Shipping
DDTC1xxGE-7	SOT-523	3000/Tape & Reel
DDTC1xxGE-13	SOT-523	10,000/Tape & Reel

- Notes:
- For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
  - For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above.  
Example: DDTC115GE-7-F.

## Marking Information



XXX = Product Type Marking Code (See Page 1, e.g. N26 = DDTC114GE)  
 YM = Date Code Marking  
 Y = Year (ex: N = 2002)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**TYPICAL CURVES - DDTC114GE**

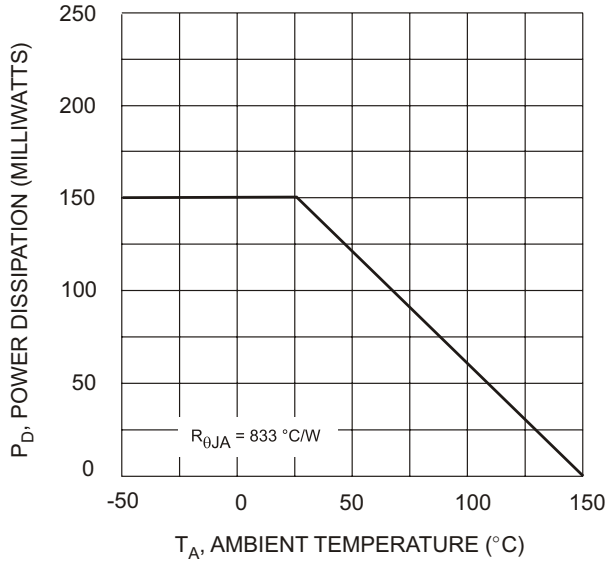


Fig. 1 Derating Curve

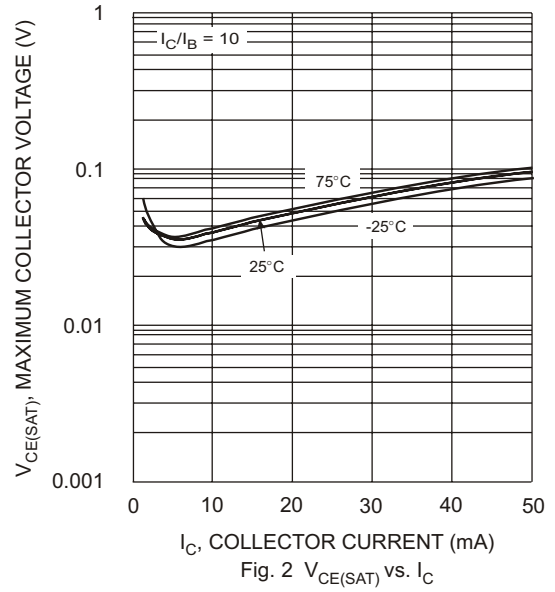


Fig. 2  $V_{CE(SAT)}$  vs.  $I_C$

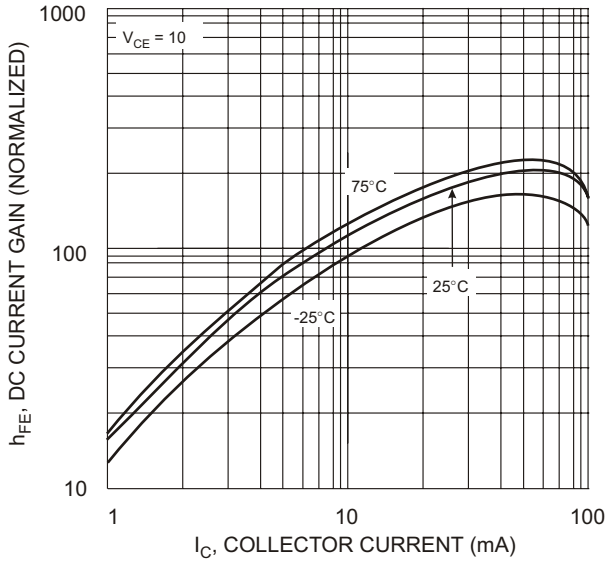


Fig. 3 DC Current Gain

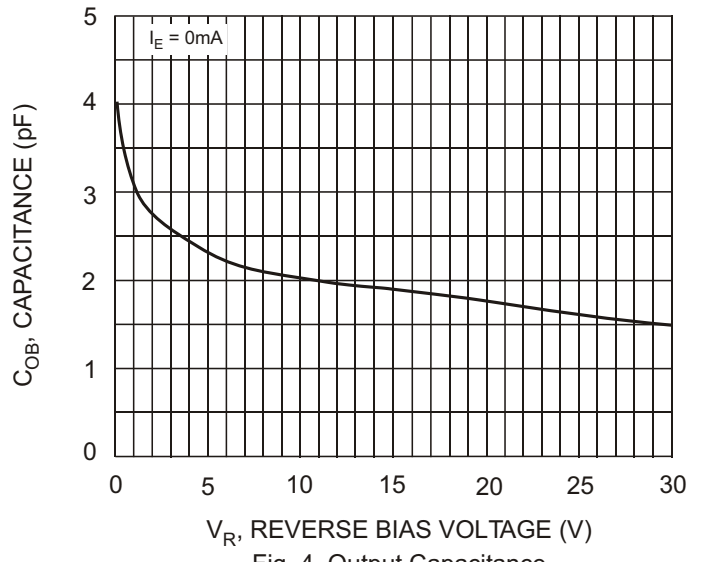


Fig. 4 Output Capacitance

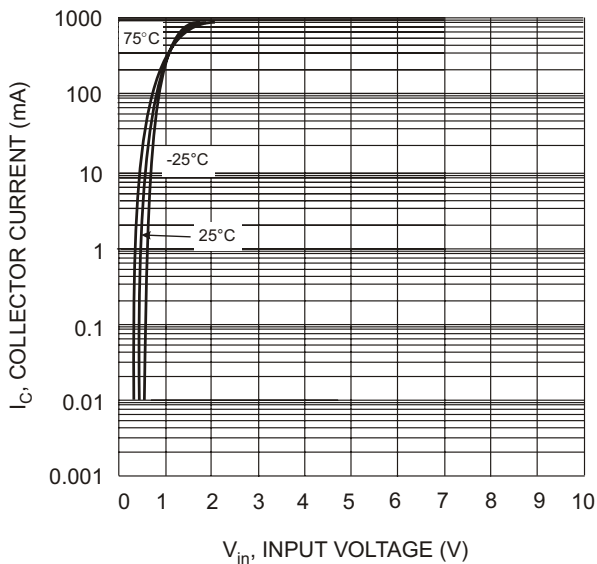


Fig. 5 Collector Current Vs. Input Voltage

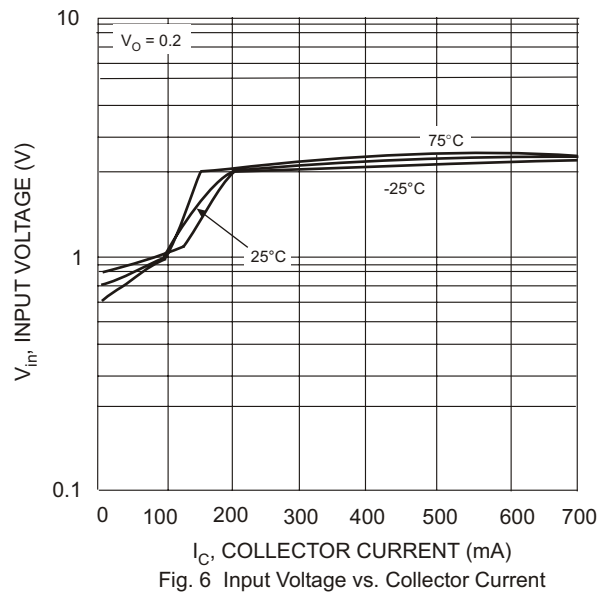


Fig. 6 Input Voltage vs. Collector Current